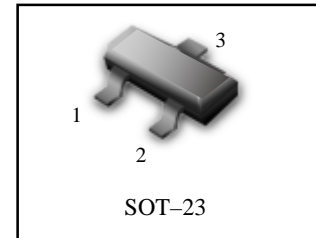


General Purpose Transistors

PNP Silicon

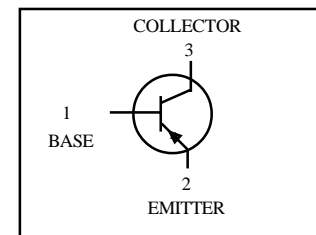
FEATURE

- High current capacity in compact package.
 $I_C = -1.5A$.
- Epitaxial planar type.
- PNP complement: FTC8050H
- Pb-Free Package is available.



DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
FTA8550H	1FD	3000/Tape&Reel



MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector-Emitter Voltag	V_{CE0}	-25	V
Collector-Base Voltag	V_{CBO}	-40	V
Emitter-Base Voltag	V_{EBO}	-5	V
Collector Current-continuou	I_C	-1500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,(1) $T_A = 25^\circ C$ Derate above $25^\circ C$	P_D	225 18	mW mW/ C
Thermal Resistance,Junction to Ambient	$R_{\theta JA}$	556	C/W
Total Device Dissipation Alumina Substrate,(2) $T_A = 25^\circ C$ Derate above $25^\circ C$	P_D	300 24	mW mW/ C
Thermal Resistance,Junction to Ambient	$R_{\theta JA}$	417	C/W
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	C



FTA8550H

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C = -1.0\text{mA}$)	$V_{(BR)CEO}$	-25	-	-	V
Emitter-Base Breakdown Voltage ($I_E = -100\mu\text{A}$)	$V_{(BR)EBO}$	-5	-	-	V
Collector-Base Breakdown Voltage ($I_E = -100\mu\text{A}$)	$V_{(BR)CBO}$	40	-	-	V
Collector Cutoff Current ($V_{CB} = -35\text{V}$)	I_{CBO}	-	-	-150	nA
Emitter Cutoff Current ($V_{EB} = 4\text{V}$)	I_{EBO}	-	-	-150	nA

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

ON CHARACTERISTICS

DC Current Gain $I_C = -100\text{mA}$, $V_{CE} = -1\text{V}$	h_{FE}	150	-	300	
Collector-Emitter Saturation Voltage ($I_C = -800\text{mA}$, $I_B = -80\text{mA}$)	$V_{CE(S)}$	-	-	-0.5	V

Typical Characteristics Curves

Fig.1- Static Characteristic

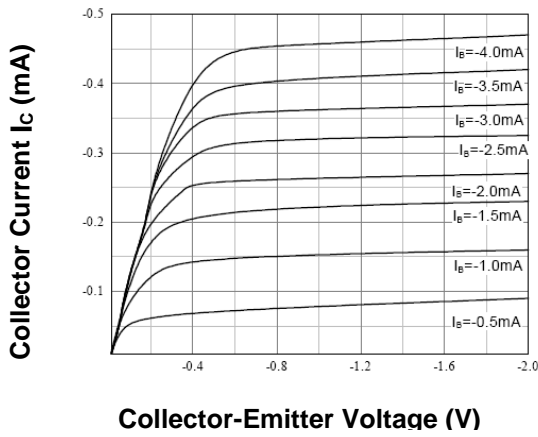
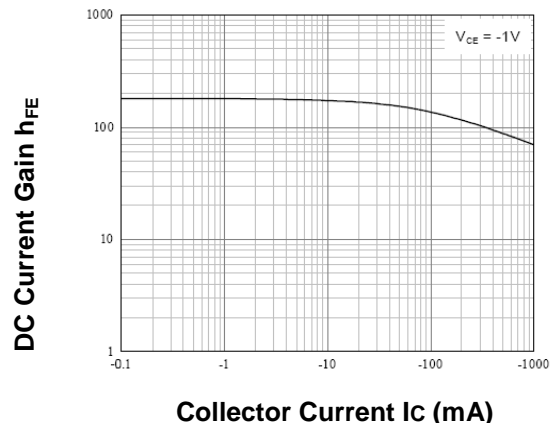


Fig.2- DC Current Gain



**Fig.3- Collector-Emitter Saturation Voltage
Base-Emitter Saturation Voltage**

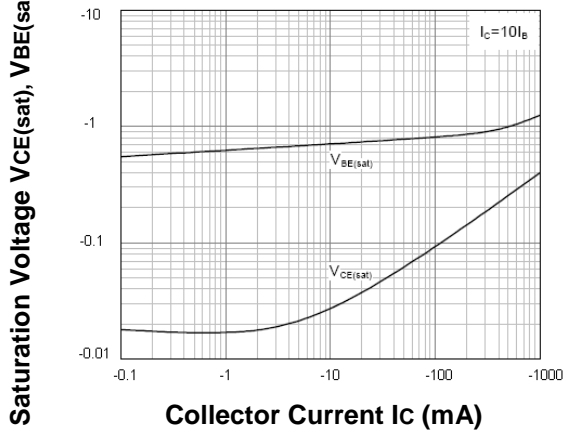


Fig.4- Base-Emitter On Voltage

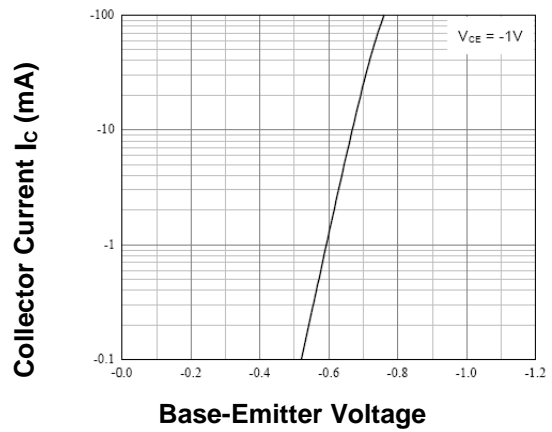
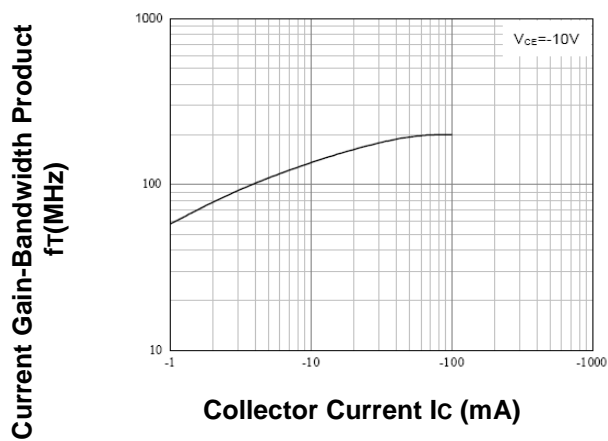


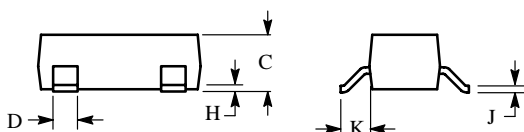
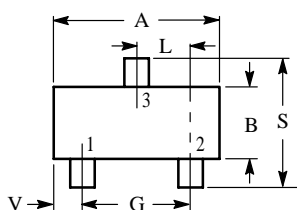
Fig.5- Current Gain Bandwidth Product



SOT-23

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

PIN 1 BASE
 2 EMITTER
 3 COLLECTOR

